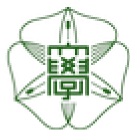

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Title	Three-dimensional deposition of TiN film using low frequency (50 Hz) plasma chemical vapor deposition
Author(s)	Shimozuma, M.; Date, H.; Iwasaki, T.; Tagashira, H.; Yoshino, M.; Yoshida, K.
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ERRATA

Erratum: "Three-dimensional deposition of TiN film using low frequency (50 Hz) plasma chemical vapor deposition" [J. Vac. Sci. Technol. A 15, 1897 (1997)]

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Due to an error in production, Fig. 1 was incorrectly printed. The correct figure is published below.

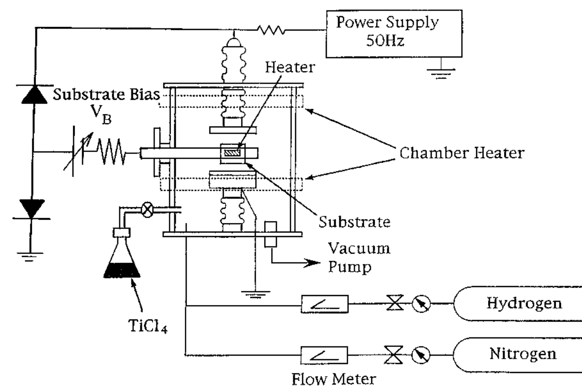

FIG. 1. Schematic diagram of the plasma CVD apparatus with substrate bias circuit using two diodes.

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